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Pages 1 to 37

INTEGRATED CIRCUITS, SILICON MONOLITHIC

BIPOLAR OPERATIONAL AMPLIFIERS

BASED ON TYPE LM 101A

ESA/SCC Detail Specification No. 9101/001



**space components
coordination group**

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**ESASCC**ESA/SCC Detail Specification
No. 9101/001

Rev 'C'

PAGE 2

ISSUE 3

DOCUMENTATION CHANGE NOTICE

Rev. Letter	Rev. Date	Reference	CHANGE Item	Approved DCR No.
		This issue supersedes Issue 2 and incorporates all modifications agreed on the basis of Policy DCR 21019 (Appendices to Detail Specifications), DCR 23058 (new Table 2, 3(a), 3(b) and Figure 4 format) and the following DCR's:-		
		P21. Table 2	: AVS, PSRR, CMRR and V_{OUT} tests moved to d.c. parameters	22110
		P34. Figure 5	: Modification of burn-in circuit	22110
'A'	Jul. '81	P20. Table 2	: Tests 1-2-3-4-5-6-7-8: In test conditions column V_{IN} modified to read $V_{IN} = 0V$	22130
		P21. Table 2	: Tests 16 and 17: In test conditions column V_{IN} modified to read $V_{IN} = 0V$	22130
		P23. Table 3(a)	: Tests 1-2-3-4-5-6-7-8: In test conditions column V_{IN} modified to read $V_{IN} = 0V$	22130
		P25. Table 3(b)	: As for Table 3(a)	22130
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'C'	Sep. '84	P1. Cover page P2. DCN page P5. Appendices P7. Table 1(a) P8. Table 1(b) P9. Figure 1 P15. Para. 2 P15. Para. 4.2.2 P17. Para. 4.4.2 P37. Appendices	: Appendix 'A' added - Lead finish redefined : Note to T_{sol} changed to 7 : Note 3, 4 and 5 derating factors amended. Format amended : Amended : MIL-STD-1276 deleted : PIND test added : Rewritten : Appendix 'A' added	None None 24037/38 21025 23107 22295 22295 21025 22240 21025 24037/38



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Rev. Letter	Rev. Date	Reference	CHANGE Item	Approved DCR No.
'D'	Dec. '91	P1. Cover page P2A. DCN : Page added P3. T of C : Para. 4.3.3 deleted P7. Table 1(a) : Variant 07 added P8. Table 1(b) : No. 4, Characteristics amended to include Variant 07 P9. Figure 1 : Note 2 amended to include Variant 07 P11. Figure 2(b) : Title amended to include Variant 07 P15. Para. 4.2.2 : Deviation deleted, "None." added P16. Para. 4.2.4 : Deviation deleted, "None." added Para. 4.2.5 : Deviation deleted, "None." added Para. 4.3.2 : Paragraph amended to include Variant 07 Para. 4.3.3 : Paragraph deleted P17. Para. 4.4.2 : Paragraph amended Para. 4.5.2 : Paragraph amended to include Variant 07	None None None 22915 22915 22915 22915 21048 22919 22919 22915 22921 22915 22915	
		This specification has been transferred from hardcopy to electronic format. The content is unchanged but minor differences in presentation exist.		

**ESC**ESA/SCC Detail Specification
No. 9101/001



Rev. 'D'

PAGE 3

ISSUE 3

TABLE OF CONTENTS



	<u>Page</u>
1. <u>GENERAL</u>	6
1.1 Scope	6
1.2 Component Type Variants	6
1.3 Maximum Ratings	6
1.4 Parameter Derating Information	6
1.5 Physical Dimensions	6
1.6 Pin Assignment	6
1.7 Truth Table	6
1.8 Circuit Schematic	6
1.9 Functional Diagram	6
2. <u>APPLICABLE DOCUMENTS</u>	15
3. <u>TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS</u>	15
4. <u>REQUIREMENTS</u>	15
4.1 General	15
4.2 Deviations from Generic Specification	15
4.2.1 Deviations from Special In-process Controls	15
4.2.2 Deviations from Final Production Tests (Chart II)	15
4.2.3 Deviations from Burn-in Tests (Chart III)	16
4.2.4 Deviations from Qualification, Environmental and Endurance Tests (Chart IV)	16
4.2.5 Deviations from Lot Acceptance Tests (Chart V)	16
4.3 Mechanical Requirements	16
4.3.1 Dimension Check	16
4.3.2 Weight	16
4.4 Materials and Finishes	16
4.4.1 Case	17
4.4.2 Lead Material and Finish	17
4.5 Marking	17
4.5.1 General	17
4.5.2 Lead Identification	17

		<p style="text-align: center;">ESA/SCC Detail Specification No. 9101/001</p>		<p>PAGE 4 ISSUE 3</p>
----------------------------------------------------------------------------------	----------------------------------------------------------------------------------	----------------------------------------------------------------------------------	--	---------------------------

	<u>Page</u>
4.5.3 The SCC Component Number	17
4.5.4 Traceability Information	17
4.5.5 Marking of Small Components	18
4.6 Electrical Characteristics	18
4.6.1 Electrical Measurements at Room Temperature	18
4.6.2 Electrical Measurements at High and Low Temperatures	18
4.6.3 Circuits for Electrical Measurements	18
4.7 Burn-in Tests	18
4.7.1 Parameter Drift Values	18
4.7.2 Conditions for H.T.R.B. and Burn-in	19
4.7.3 Electrical Circuits for H.T.R.B. and Burn-in	19
4.8 Environmental and Endurance Tests	35
4.8.1 Electrical Measurements on Completion of Environmental Tests	35
4.8.2 Electrical Measurements at Intermediate Points During Endurance Tests	35
4.8.3 Electrical Measurements on Completion of Endurance Tests	35
4.8.4 Conditions for Operating Life Tests	35
4.8.5 Electrical Circuits for Operating Life Tests	35
4.8.6 Conditions for High Temperature Storage Test	35

TABLES

1(a) Type Variants	7
1(b) Maximum Ratings	8
2 Electrical Measurements at Room Temperature, d.c. Parameters	20
Electrical Measurements at Room Temperature, a.c. Parameters	22
3(a) Electrical Measurements at High Temperature	23
3(b) Electrical Measurements at Low Temperature	25
4 Parameter Drift Values	33
5 Conditions for Burn-in	33
6 Electrical Measurements on Completion of Environmental Tests and at Intermediate Points and on Completion of Environmental Testing	36

 	<p style="text-align: center;">ESA/SCC Detail Specification No. 9101/001</p>	<p style="text-align: center;">Rev. 'C'</p>	<p style="text-align: right;">PAGE 5 ISSUE 3</p>
-------------------------------------------------------------------------------------------------------------------------------------------------------------------	----------------------------------------------------------------------------------	---------------------------------------------	------------------------------------------------------

FIGURES

Page

1	Device Dissipation Derating with Temperature	9
2	Physical Dimensions	10
3(a)	Pin Assignment	13
3(b)	Truth Table	N/A
3(c)	Circuit Schematic	13
3(d)	Functional Diagram	14
4(a)	Input Offset Voltage	27
4(b)	Input Offset Current	27
4(c)	Input (Plus) Bias Current	28
4(d)	Input (Minus) Bias Current	28
4(e)	Supply Current	29
4(f)	Short Circuit Output Current	29
4(g)	Output Voltage Swing and Open Loop Voltage Gain	30
4(h)	Power Supply Rejection Ratio	30
4(i)	Common Mode Rejection Ratio	31
4(j)	Dynamic Test Measurement Circuit	32
5	Electrical Circuit for Burn-in and Operating Life Test	34

APPENDICES (Applicable to specific Manufacturers only)

'A'	Agreed Deviations for Motorola (F)	37
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**1. GENERAL****1.1 SCOPE**

This specification details the ratings, physical and electrical characteristics, test and inspection data for a silicon monolithic, bipolar operational amplifier, based on Type LM 101A. It shall be read in conjunction with ESA/SCC Generic Specification No. 9000, the requirements of which are supplemented herein.

1.2 COMPONENT TYPE VARIANTS

Variants of the basic type integrated circuits specified herein, which are also covered by this specification, are given in Table 1(a).

1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the integrated circuits specified herein, are as scheduled in Table 1(b).

1.4 PARAMETER DERATING INFORMATION

As per Figure 1.

1.5 PHYSICAL DIMENSIONS

As per Figure 2.

1.6 PIN ASSIGNMENT

As per Figure 3(a).

1.7 TRUTH TABLE (FIGURE 3(b))

Not applicable.

1.8 CIRCUIT SCHEMATIC

As per Figure 3(c).

1.9 FUNCTIONAL DIAGRAM

As per Figure 3(d).

TABLE 1(a) - TYPE VARIANTS

DASH No.	CASE	FIGURE	LEAD FINISH
-01	FLAT	2(a)	D2
-02	FLAT	2(a)	D3 or D4
-03	TO99	2(b)	D2
-04	TO99	2(b)	D3 or D4
-05	DIL	2(c)	D2
-06	DIL	2(c)	D3 or D4
-07	TO99	2(b)	D9



 	ESA/SCC Detail Specification No. 9101/001	Rev. 'D'	PAGE 8
			ISSUE 3

TABLE 1(b) - MAXIMUM RATINGS

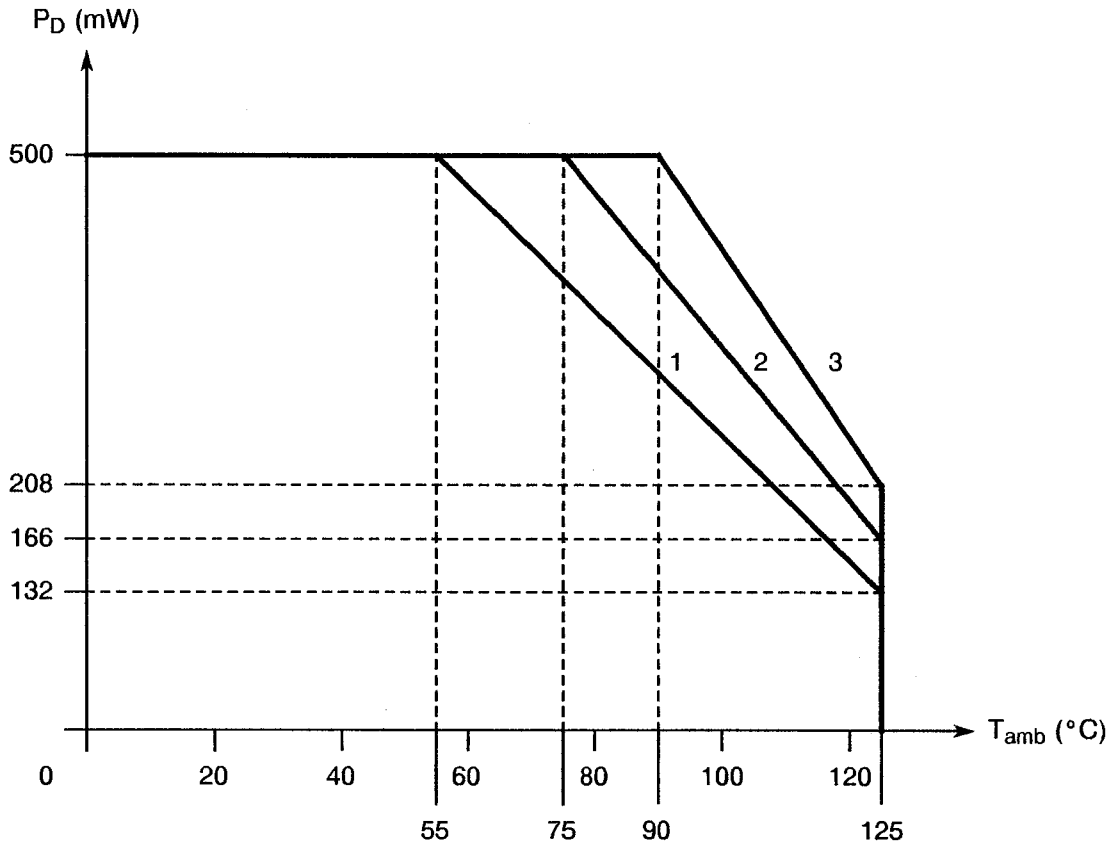
No.	CHARACTERISTICS	SYMBOL	MAXIMUM RATINGS	UNITS	REMARKS
1	Supply Voltage Range	V_S	± 22	V	
2	Differential Input Voltage Range	V_{ID}	± 30	V	Note 1
3	Input Voltage Range	V_I	± 15	V	Note 2
4	Device Power Dissipation - Type Variants 01-02 - Type Variants 03-04-07 - Type Variants 05-06	P_D	500	mW	Note 3 Note 4 Note 5
5	Output Short Circuit Duration	-	Indefinite	mW	Note 6
6	Operating Temperature Range	T_{amb}	- 55 to + 125	$^{\circ}C$	
7	Storage Temperature Range	T_{stg}	- 55 to + 150	$^{\circ}C$	
8	Soldering Temperature	T_{sol}	+ 300	$^{\circ}C$	Note 7
9	Junction Temperature	T_j	+ 150	$^{\circ}C$	

NOTES

1. The inputs are shunted with back-to-back diodes for overvoltage protection. Therefore, excessive current will flow if a differential voltage in excess of 1.0V is applied between the inputs, unless some limiting resistance is used.
2. If the supply voltage is less than +15V, the maximum input voltage is equal to the supply voltage.
3. Derate above $T_{amb} = +55^{\circ}C$ at 5.26mW/ $^{\circ}C$. See Figure 1.
4. Derate above $T_{amb} = +75^{\circ}C$ at 6.67mW/ $^{\circ}C$. See Figure 1.
5. Derate above $T_{amb} = +90^{\circ}C$ at 8.33mW/ $^{\circ}C$. See Figure 1.
6. Continuous short circuit is allowed for an ambient temperature of +70 $^{\circ}C$ and a case temperature of +125 $^{\circ}C$.
7. Duration: 10 seconds. Distance from case: 1.5mm.



FIGURE 1 - DEVICE DISSIPATION DERATING WITH TEMPERATURE



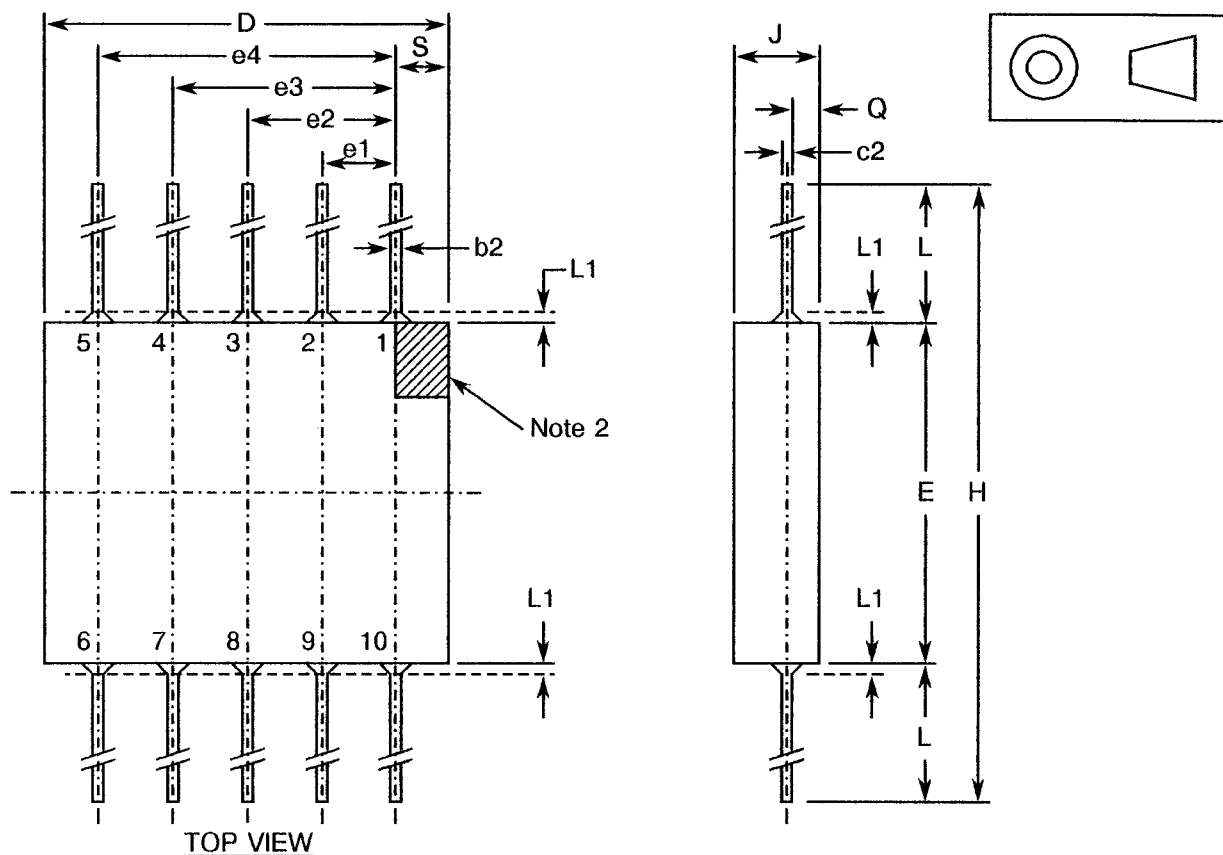
NOTES

1. Derating for type variants 01 and 02.
2. Derating for type variants 03, 04 and 07.
3. Derating for type variants 05 and 06.



FIGURE 2 - PHYSICAL DIMENSIONS

FIGURE 2(a) - VARIANTS 01 AND 02, FLAT PACKAGE TO91



The metric dimensions are calculated from the original dimensions in inches.

SYMBOL	MILLIMETRES		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
b2	0.254	0.482	0.010	0.019	
c2	0.077	0.152	0.003	0.006	
D	6.10	6.98	0.240	0.275	
E	6.10	6.60	0.240	0.260	
e1	1.15	1.39	0.045	0.055	1
e2	2.42	2.66	0.095	0.105	1
e3	3.69	3.93	0.145	0.155	1
e4	4.96	5.20	0.195	0.205	1
H	13.72	19.81	0.540	0.780	
J	0.77	1.77	0.030	0.070	
L	3.81	6.60	0.150	0.260	
L1	-	0.38	-	0.015	
Q	0.13	0.83	0.005	0.035	
S	0.52	0.86	0.020	0.035	

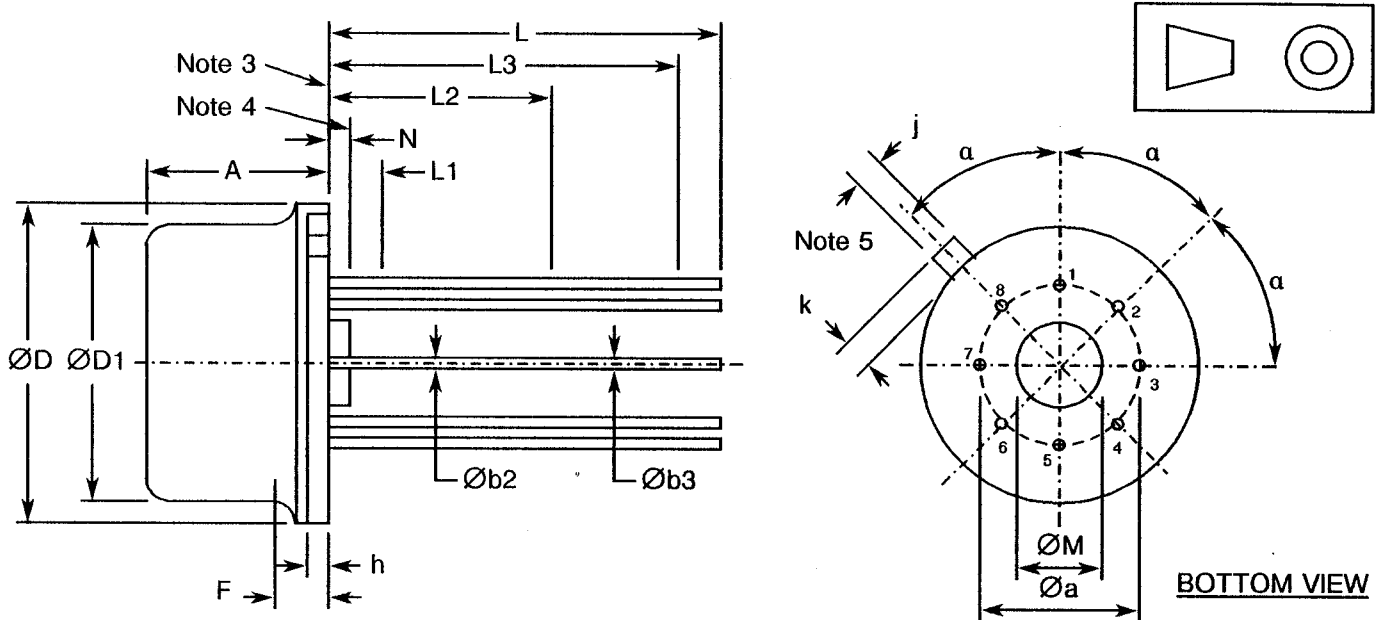
NOTES

1. The space between terminals has to be measured at a distance of 0.76mm maximum (0.030 inch) from where the terminals emerge from the case.
2. The top face and Pin No. 1 are marked.



FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(b) - VARIANTS 03, 04 AND 07, METAL CAN TO99



SYMBOL	MILLIMETRES			INCHES			DEGR. NOM.	NOTES
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
Øa	-	5.08 (*)	-	-	0.200 (*)	-		1
A	4.20	-	4.69	0.165	-	0.185		
Øb2	0.407	-	0.508	0.016	-	0.020		
Øb3	-	-	0.53	-	-	0.021		
ØD	8.51	-	9.39	0.335	-	0.370		
ØD1	7.75	-	8.50	0.305	-	0.335		
F	-	-	1.27	-	-	0.050		
h	0.15	-	1.01	0.006	-	0.040		
j	0.712	-	0.863	0.028	-	0.034		
k	0.74	-	1.14	0.029	-	0.045		2
L	12.50	-	14.50	0.492	-	0.071		
L1	-	-	1.27	-	-	0.050		
L2	6.35	-	-	0.250	-	-		
L3	12.70	-	-	0.500	-	-		
ØM	3.56	-	4.06	0.140	-	0.160		
N	0.26	-	1.01	0.010	-	0.040		
α							45° (*)	1

NOTES

1. The section of each terminal, from a distance of 1.37mm (0.054 inch) to the reference plane, shall be located in a ring whose diameter is 0.99mm (0.039 inch), centred on the accurate geometrical point defining the terminal axis.
2. Measured from the D diameter.
3. Reference plane.
4. Base plane.
5. Reference index of Pin 8.

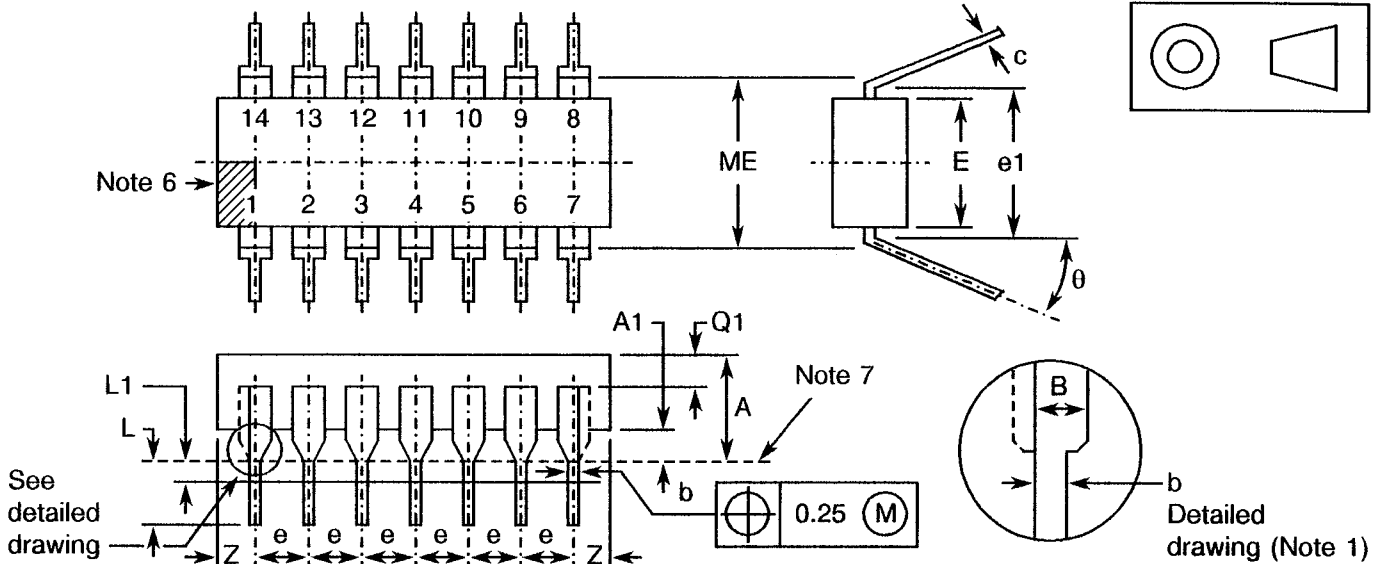
* = accurate geometrical location.

The metric dimensions are calculated from the original dimensions in inches.



FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(c) - VARIANTS 05 AND 06, DUAL-IN-LINE PACKAGE TO116



SYMBOL	MILLIMETRES			INCHES			DEGREES		NOTES
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	MAX.	
A	-	-	5.08	-	-	0.200			
A1	0.51	-	-	0.020	-	-			
B	-	-	1.77	-	-	0.070			1
b	0.381	-	0.508	0.015	-	0.020			1
c	0.204	-	0.304	0.008	-	0.012			
E	-	6.3	-	-	0.25	-			
e	-	2.54 *	-	-	0.100 *	-			2
e1	-	7.62 *	-	-	0.300 *	-			3
L	2.5	-	3.9	0.098	-	0.154			(a)
L1	-	-	0.76	-	-	0.030			
ME	7.62	-	8.25	0.300	-	0.325			3
Q1	-	-	2.03	-	-	0.080			
Z									4
θ							0	15	
n =	7 x 2								5

NOTES

- The lead profile is not required for transition from B to b. The outline of the extreme outputs in the case of F.105A may differ from that of the others, as shown in the Figure.
- The space between leads is measured on the area L1.
- Measured when the value of the angle θ is zero.
- Case F.105: Z between $e/2$ and e ($1.27\text{mm} < Z < 2.54\text{mm}$).
Case F.105A: Z less than $e/2$ ($Z < 1.27\text{mm}$).
- n = quantity of leads.
- Area for visible reference mark on top face.
- Base plane.
* = accurate geometrical location.
- (a) Recommended dimensions for the future: minimum 3.0mm (0.122 inch).
maximum 3.9mm (0.154 inch).

The metric dimensions are calculated from the original dimensions in inches.



FIGURE 3(a) - PIN ASSIGNMENT

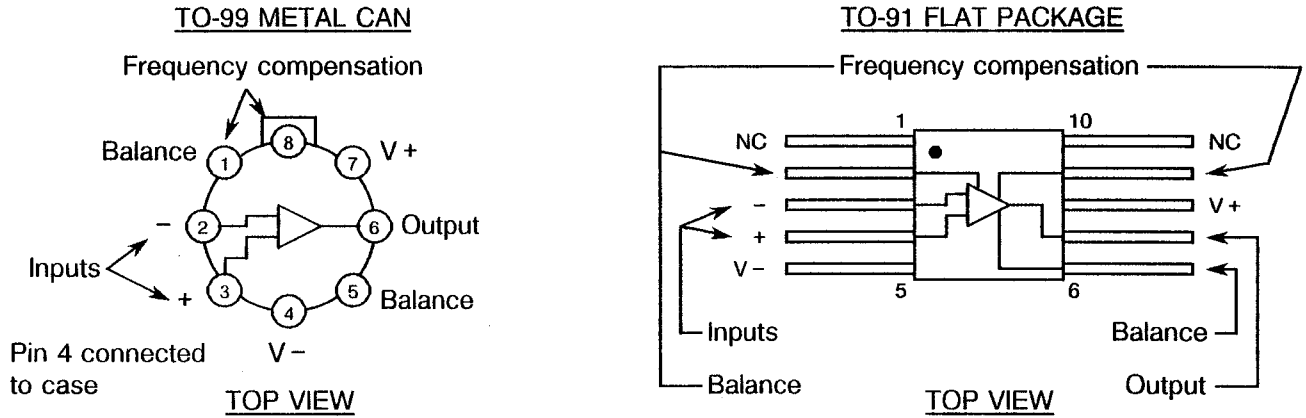
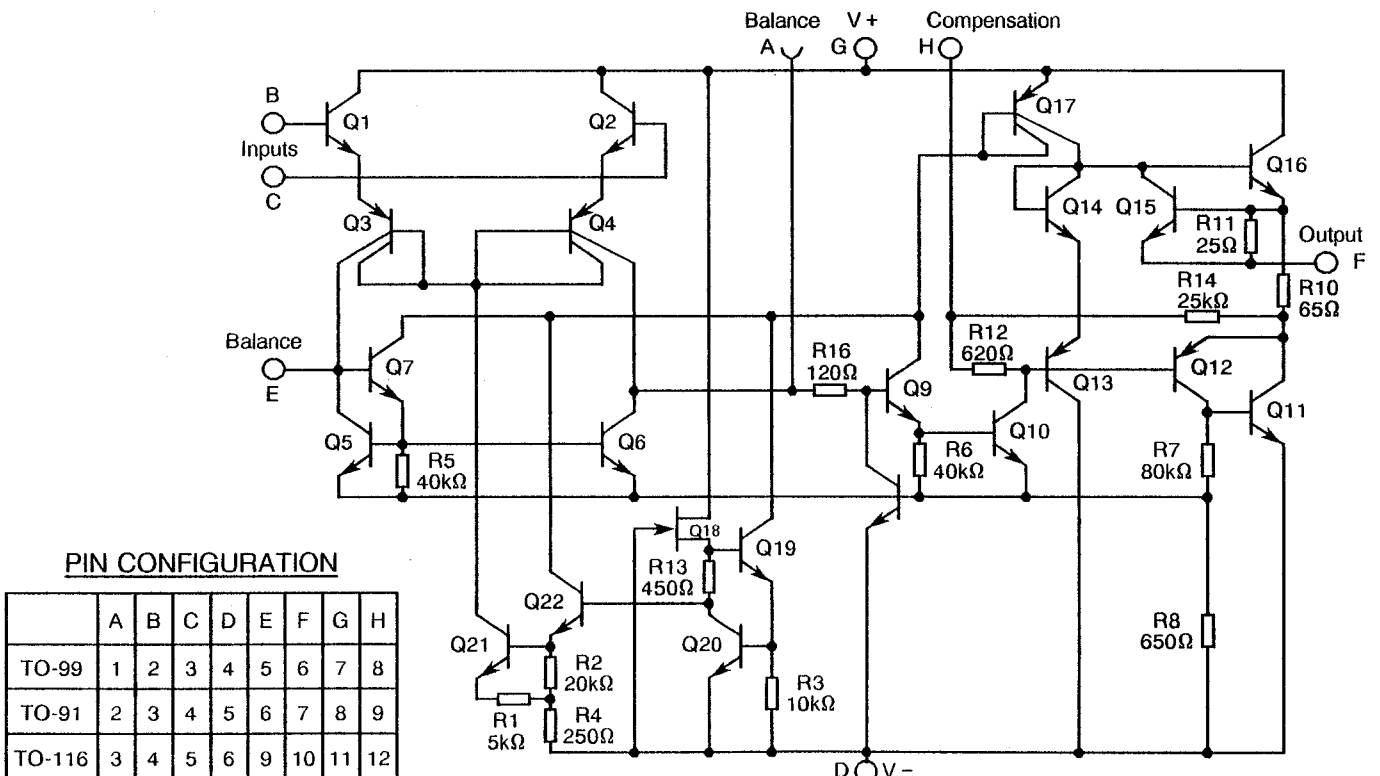


FIGURE 3(b) - TRUTH TABLE

Not applicable.

FIGURE 3(c) - CIRCUIT SCHEMATIC (FOR INFORMATION ONLY)

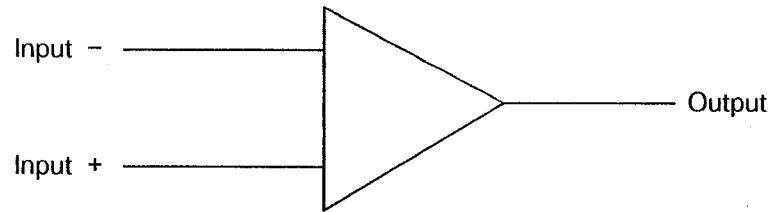


PIN CONFIGURATION

	A	B	C	D	E	F	G	H
TO-99	1	2	3	4	5	6	7	8
TO-91	2	3	4	5	6	7	8	9
TO-116	3	4	5	6	9	10	11	12



FIGURE 3(d) - FUNCTIONAL DIAGRAM



**2. APPLICABLE DOCUMENTS**

The following documents form part of this specification and shall be read in conjunction with it:-

- (a) ESA/SCC Generic Specification No. 9000 for Integrated Circuits.
- (b) MIL-STD-883, Test Methods and Procedures for Micro-electronics.

3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply. In addition, the following abbreviations are used:-

- K_{OV} = Overshoot.
- S_{VR} = Supply Voltage Rejection Ratio.
- V_{OM} = Maximum Range of Output Voltage.
- I_{OS} = Output Short Circuit Current.
- I_{CC} = Supply Current.

4. REQUIREMENTS**4.1 GENERAL**

The complete requirements for procurement of the integrated circuits specified herein are stated in this specification and ESA/SCC Generic Specification No. 9000 for Integrated Circuits. Deviations from the Generic Specification applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

4.2 DEVIATIONS FROM GENERIC SPECIFICATION

The following deviations from ESA/SCC Generic Specification No. 9000 shall apply:-

4.2.1 Deviations from Special In-process Controls

None.

4.2.2 Deviations from Final Production Tests (Chart II)

None.

**4.2.3 Deviations from Burn-in Tests (Chart III)**

Subpara. 7.1.1(a), "High Temperature Reverse Bias" test and subsequent electrical measurements related to this test shall be omitted.

4.2.4 Deviations from Qualification, Environmental and Endurance Tests (Chart IV)

None.

4.2.5 Deviations from Lot Acceptance Tests (Chart V)

None.

4.3 MECHANICAL REQUIREMENTS**4.3.1 Dimension Check**

The dimensions of the integrated circuits specified herein shall be checked. They shall conform to those shown in Figure 2.

4.3.2 Weight

The maximum weight of the integrated circuits specified herein shall be for:-

Variants 01, 02: 0.35 grammes.

Variants 03, 04 and 07: 1.50 grammes.

Variants 05, 06: 2.00 grammes.

4.4 MATERIALS

The materials shall be as specified herein. Where a definite material is not specified, a material which will enable the integrated circuits specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.



4.4.1 Case

The case shall be hermetically sealed and have a metal body with hard glass seals or a ceramic body and the lids shall be welded, brazed, preform-soldered or glass frit-sealed.

4.4.2 Lead Material and Finish

The leads shall be Type 'D' with either Type '2', Type '3 or 4' or Type '9' finish in accordance with ESA/SCC Basic Specification No. 23500 (See Table 1(a) for Type Variants).

4.5 MARKING

4.5.1 General

The marking of components delivered to this specification shall be in accordance with ESA/SCC Basic Specification No. 21700. Each component shall be marked in respect of:-

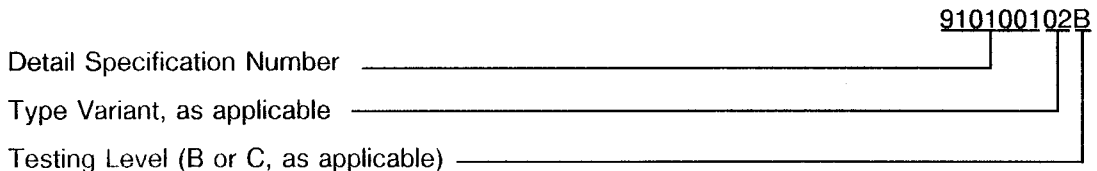
- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

4.5.2 Lead Identification

An index shall be located at the top of the package in the position defined in Note 2 of Figure 2 (Variants 01, 02), Note 5 of Figure 2 (Variants 03, 04, 07) or Note 6 of Figure 2 (Variants 05, 06). Alternatively, a tab may be used to identify Pin No. 1. The pin numbering shall be read with the index or tab on the left-hand side.

4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:



4.5.4 Traceability Information

Each component shall be marked in respect of traceability information in accordance with ESA/SCC Basic Specification No. 21700.



4.5.5 Marking of Small Components

When it is considered that the component is too small to accommodate the marking as specified above, as much as space permits shall be marked. The order of precedence shall be as follows:-

- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

The marking information in full shall accompany each component in its primary package.

4.6 ELECTRICAL CHARACTERISTICS

4.6.1 Electrical Measurements at Room Temperature

The parameters to be measured in respect of electrical characteristics are scheduled in Table 2. Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.6.2 Electrical Measurements at High and Low Temperatures

The parameters to be measured at high and low temperatures are scheduled in Tables 3(a) and 3(b). The measurements shall be performed at $T_{amb} = +125$ °C and -55 °C respectively.


4.6.3 Circuits for Electrical Measurements

Circuits for use in performing the electrical measurements listed in Tables 2 and 3 of this specification are shown in Figure 4.

4.7 BURN-IN TESTS

4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, measurements shall be performed at $T_{amb} = +22 \pm 3$ °C. The parameter drift values (Δ) applicable to the parameters scheduled, shall not be exceeded. In addition to these drift value requirements, the appropriate limit value specified for a given parameter in Table 2 shall not be exceeded.

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4.7.2 Conditions for Burn-in

The requirements for burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 9000. The conditions for burn-in shall be as specified in Table 5 of this specification.

4.7.3 Electrical Circuits for Burn-in

Circuits for use in performing the burn-in tests are shown in Figure 5 of this specification.

**TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS**

No.	Characteristics	Symbol	Test Method MIL-STD 883	Test Fig.	Meas'd Value	Test Conditions	Limits		Unit
							Min	Max	
1	Input Offset Voltage	V_{IO1}	4001	4(a)	E_1 (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $V_{IN} = 0V$	-	2.0	mV
2	Input Offset Voltage	V_{IO2}	4001	4(a)	E_2 (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ $V_{IN} = 0V$	-	2.0	mV
3	Input Offset Current	I_{IO1}	4001	4(b)	E_3 (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $R_S = 100k, V_{IN} = 0V$	-	10	nA
4	Input Offset Current	I_{IO2}	4001	4(b)	E_4 (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ $R_S = 100k, V_{IN} = 0V$	-	10	nA
5	Input (Plus) Bias Current	I_{+IB1}	4001	4(c)	E_5 (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $R_S = 100k, V_{IN} = 0V$	-	75	nA
6	Input (Plus) Bias Current	I_{+IB2}	4001	4(c)	E_6 (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ $R_S = 100k, V_{IN} = 0V$	-	75	nA
7	Input (Minus) Bias Current	I_{-IB1}	4001	4(d)	E_7 (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $R_S = 100k, V_{IN} = 0V$	-	75	nA
8	Input (Minus) Bias Current	I_{-IB2}	4001	4(d)	E_8 (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ $R_S = 100k, V_{IN} = 0V$	-	75	nA
9	Power Supply Current	$I_{CC(-)}$	4005	4(e)	I_{CC}	$+V_{CC} = +20V, -V_{CC} = -20V$	-	3.0	mA
10	Short Circuit Output Current (Plus)	$I_{OS(+)}$	3011	4(f)	I_{OS}	$+V_{CC} = +15V, -V_{CC} = -15V$ $V_{IN} = -15V$ Note 1	-40	-9.0	mA
11	Short Circuit Output Current (Minus)	$I_{OS(-)}$	3011	4(f)	I_{OS}	$+V_{CC} = +15V, -V_{CC} = -15V$ $V_{IN} = +15V$ Note 1	9.0	40	mA
12	Open Loop Voltage Gain (Plus)	$+A_{VS}$	4004	4(g)	E_9 (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $V_{IN} = -15V, R_L = 2.0k$	50	-	V/mV
13	Open Loop Voltage Gain (Minus)	$-A_{VS}$	4004	4(g)	E_{10} (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $V_{IN} = +15V, R_L = 2.0k$	50	-	V/mV

NOTES: See Page 22.



TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS (CONT'D)

No.	Characteristics	Symbol	Test Method MIL-STD 883	Test Fig.	Meas'd Value	Test Conditions	Limits		Unit
							Min	Max	
14	Open Loop Voltage Gain (Plus)	+A _{VS}	4004	4(g)	E ₁₁ (V)	+V _{CC} = +5.0V, -V _{CC} = -5.0V V _{IN} = -2.0V, R _L = 2.0k	10	-	V/mV
15	Open Loop Voltage Gain (Minus)	-A _{VS}	4004	4(g)	E ₁₂ (V)	+V _{CC} = +5.0V, -V _{CC} = -5.0V V _{IN} = +2.0V, R _L = 2.0k	10	-	V/mV
16	Power Supply Rejection Ratio (Plus)	+PSRR	4003	4(h)	E ₁₃ (V)	+V _{CC} = 10V, -V _{CC} = -20V V _{IN} = 0V	100	-	V/V
17	Power Supply Rejection Ratio (Minus)	-PSRR	4003	4(h)	E ₁₄ (V)	+V _{CC} = 20V, -V _{CC} = -10V V _{IN} = 0V	100	-	V/V
18	Common Mode Rejection Ratio	CMRR	4003	4(i)	E ₁₅ (V)	+V _{CC} = 35V, -V _{CC} = -5.0V V _{IN} = -15V	80	-	dB
19					E ₁₆ (V)	+V _{CC} = 5.0V, -V _{CC} = -35V V _{IN} = 15V			
20	Output Voltage Swing (Plus)	V _{OUT(+)}	4004	4(g)	E ₁₇ (V)	+V _{CC} = 20V, -V _{CC} = -20V V _{IN} = -20V, R _L = 2.0k	15	-	V
21	Output Voltage Swing (Minus)	V _{OUT(-)}	4004	4(g)	E ₁₈ (V)	+V _{CC} = 20V, -V _{CC} = -20V V _{IN} = +20V, R _L = 2.0k	-	-15	V

NOTES: See Page 22.

**TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - a.c. PARAMETERS**

No.	Characteristics	Symbol	Test Method MIL-STD 883	Test Fig.	Test Conditions	Limits		Unit
						Min	Max	
22	Slew Rate (Plus)	SR(+)	4002	4(j)	+ V _{CC} = ± 20V V _{IN} = - 5.0V to + 5.0V square R _L = 2.0k Note 2	0.3	-	V/μs
23	Slew Rate (Minus)	SR(-)	4002	4(j)	+ V _{CC} = ± 20V V _{IN} = - 5.0V to + 5.0V square R _L = 2.0k Note 2	0.3	-	V/μs
24	RiseTime	RT	4002	4(j)	V _{CC} = ± 20V, V _{IN} = 50mV R _L = 2.0k Note 2	-	800	ns
25	Overshoot	OS	4002	4(j)	V _{CC} = ± 20V, V _{IN} = 50mV R _L = 2.0k Note 2	-	20	%

NOTES

1. For sampling inspections and end point tests the duration of measurement of I_{OS} shall be 5 seconds minimum. For other tests, this duration may be reduced to be consistent with automatic test procedures provided that the same limits are maintained.
2. Sample Test Inspection Level = II, AQL = 2.5%.



TABLE 3(a) - ELECTRICAL MEASUREMENTS AT HIGH TEMPERATURE, +125(+0 - 5) °C

No.	Characteristics	Symbol	Test Method MIL-STD 883	Test Fig.	Meas'd Value	Test Conditions	Limits		Unit
							Min	Max	
1	Input Offset Voltage	V_{IO1}	4001	4(a)	E_1 (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $V_{IN} = 0V$	-	3.0	mV
2	Input Offset Voltage	V_{IO2}	4001	4(a)	E_2 (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ $V_{IN} = 0V$	-	3.0	mV
3	Input Offset Current	I_{IO1}	4001	4(b)	E_3 (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $R_S = 100k, V_{IN} = 0V$	-	20	nA
4	Input Offset Current	I_{IO2}	4001	4(b)	E_4 (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ $R_S = 100k, V_{IN} = 0V$	-	20	nA
5	Input (Plus) Bias Current	I_{+IB1}	4001	4(c)	E_5 (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $R_S = 100k, V_{IN} = 0V$	-	100	nA
6	Input (Plus) Bias Current	I_{+IB2}	4001	4(c)	E_6 (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ $R_S = 100k, V_{IN} = 0V$	-	100	nA
7	Input (Minus) Bias Current	I_{-IB1}	4001	4(d)	E_7 (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $R_S = 100k, V_{IN} = 0V$	-	100	nA
8	Input (Minus) Bias Current	I_{-IB2}	4001	4(d)	E_8 (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ $R_S = 100k, V_{IN} = 0V$	-	100	nA
9	Power Supply Current	$I_{CC(-)}$	4005	4(e)	I_{CC}	$+V_{CC} = +20V, -V_{CC} = -20V$	-	2.5	mA
10	Short Circuit Output Current (Plus)	$I_{OS(+)}$	3011	4(f)	I_{OS}	$+V_{CC} = +15V, -V_{CC} = -15V$ $V_{IN} = -15V$ Note 1	-40	-9.0	mA
11	Short Circuit Output Current (Minus)	$I_{OS(-)}$	3011	4(f)	I_{OS}	$+V_{CC} = +15V, -V_{CC} = -15V$ $V_{IN} = +15V$ Note 1	9.0	40	mA
12	Open Loop Voltage Gain (Plus)	$+A_{VS}$	4004	4(g)	E_9 (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $V_{IN} = -15V, R_L = 2.0k$	25	-	V/mV
13	Open Loop Voltage Gain (Minus)	$-A_{VS}$	4004	4(g)	E_{10} (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $V_{IN} = +15V, R_L = 2.0k$	25	-	V/mV

NOTES: See Page 22.

**TABLE 3(a) - ELECTRICAL MEASUREMENTS AT HIGH TEMPERATURE, +125(+0-5) °C (CONT'D)**

No.	Characteristics	Symbol	Test Method MIL-STD 883	Test Fig.	Meas'd Value	Test Conditions	Limits		Unit
							Min	Max	
20	Output Voltage Swing (Plus)	V _{OUT(+)}	4004	4(g)	E ₁₇ (V)	+V _{CC} = 20V, -V _{CC} = -20V V _{IN} = -20V, R _L = 2.0k	15	-	V
21	Output Voltage Swing (Minus)	V _{OUT(-)}	4004	4(g)	E ₁₈ (V)	+V _{CC} = 20V, -V _{CC} = -20V V _{IN} = +20V, R _L = 2.0k	-	-15	V

NOTES: See Page 22.



TABLE 3(b) - ELECTRICAL MEASUREMENTS AT LOW TEMPERATURE, -55(+5-0) °C

No.	Characteristics	Symbol	Test Method MIL-STD 883	Test Fig.	Meas'd Value	Test Conditions	Limits		Unit
							Min	Max	
1	Input Offset Voltage	V_{IO1}	4001	4(a)	E_1 (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $V_{IN} = 0V$	-	3.0	mV
2	Input Offset Voltage	V_{IO2}	4001	4(a)	E_2 (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ $V_{IN} = 0V$	-	3.0	mV
3	Input Offset Current	I_{IO1}	4001	4(b)	E_3 (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $R_S = 100k, V_{IN} = 0V$	-	20	nA
4	Input Offset Current	I_{IO2}	4001	4(b)	E_4 (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ $R_S = 100k, V_{IN} = 0V$	-	20	nA
5	Input (Plus) Bias Current	I_{+IB1}	4001	4(c)	E_5 (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $R_S = 100k, V_{IN} = 0V$	-	100	nA
6	Input (Plus) Bias Current	I_{+IB2}	4001	4(c)	E_6 (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ $R_S = 100k, V_{IN} = 0V$	-	100	nA
7	Input (Minus) Bias Current	I_{-IB1}	4001	4(d)	E_7 (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $R_S = 100k, V_{IN} = 0V$	-	100	nA
8	Input (Minus) Bias Current	I_{-IB2}	4001	4(d)	E_8 (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ $R_S = 100k, V_{IN} = 0V$	-	100	nA
9	Power Supply Current	$I_{CC(-)}$	4005	4(e)	I_{CC}	$+V_{CC} = +20V, -V_{CC} = -20V$	-	3.75	mA
10	Short Circuit Output Current (Plus)	$I_{OS(+)}$	3011	4(f)	I_{OS}	$+V_{CC} = +15V, -V_{CC} = -15V$ $V_{IN} = -15V$ Note 1	-55	-9.0	mA
11	Short Circuit Output Current (Minus)	$I_{OS(-)}$	3011	4(f)	I_{OS}	$+V_{CC} = +15V, -V_{CC} = -15V$ $V_{IN} = +15V$ Note 1	9.0	55	mA
12	Open Loop Voltage Gain (Plus)	$+A_{VS}$	4004	4(g)	E_9 (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $V_{IN} = -15V, R_L = 2.0k$	25	-	V/mV
13	Open Loop Voltage Gain (Minus)	$-A_{VS}$	4004	4(g)	E_{10} (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $V_{IN} = +15V, R_L = 2.0k$	25	-	V/mV

NOTES: See Page 22.



ESASCC

ESA/SCC Detail Specification
No. 9101/001

PAGE 26

ISSUE 3

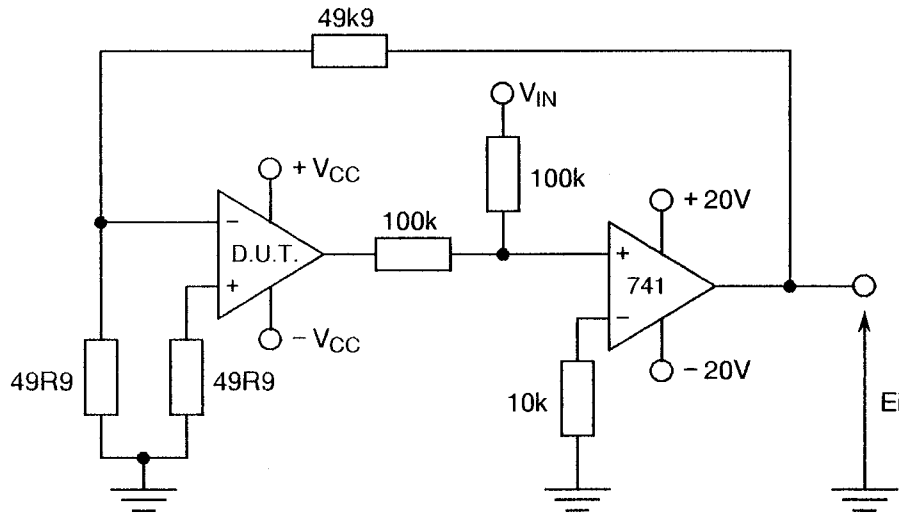
TABLE 3(b) - ELECTRICAL MEASUREMENTS AT LOW TEMPERATURE, -55(+5-0) °C (CONT'D)

No.	Characteristics	Symbol	Test Method MIL-STD 883	Test Fig.	Meas'd Value	Test Conditions	Limits		Unit
							Min	Max	
20	Output Voltage Swing (Plus)	V _{OUT(+)}	4004	4(g)	E ₁₇ (V)	+V _{CC} = 20V, -V _{CC} = -20V V _{IN} = -20V, R _L = 2.0k	15	-	V
21	Output Voltage Swing (Minus)	V _{OUT(-)}	4004	4(g)	E ₁₈ (V)	+V _{CC} = 20V, -V _{CC} = -20V V _{IN} = +20V, R _L = 2.0k	-	-15	V

NOTES: See Page 22.



FIGURE 4(a) - INPUT OFFSET VOLTAGE

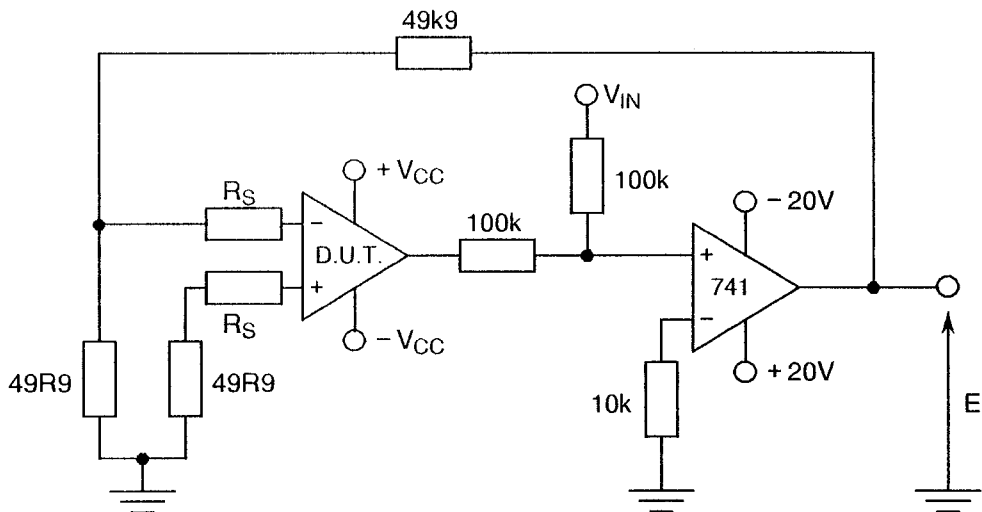


$$V_{IO1} \text{ (mV)} = E_1 \text{ (V)}, V_{IO2} \text{ (mV)} = E_2 \text{ (V)}.$$

NOTES

1. All resistors to be 0.1% tolerance.

FIGURE 4(b) - INPUT OFFSET CURRENT



$$I_{IO1} \text{ (nA)} = \frac{(E_1 \text{ (V)} - E_3 \text{ (V)}) 10^6}{R_S \text{ (k}\Omega)}$$

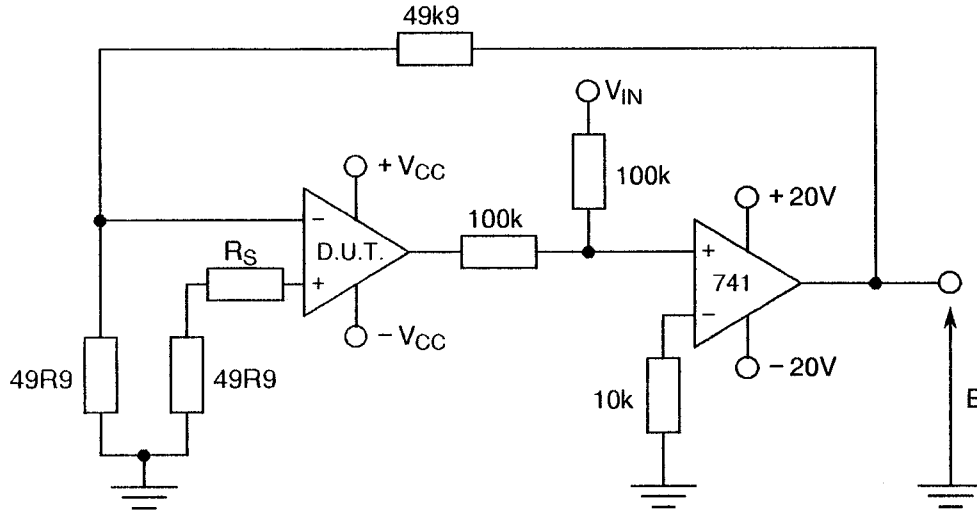
$$I_{IO2} \text{ (nA)} = \frac{(E_2 \text{ (V)} - E_4 \text{ (V)}) 10^6}{R_S \text{ (k}\Omega)}$$

NOTES

1. All resistors to be 0.1% tolerance.



FIGURE 4(c) - INPUT (PLUS) BIAS CURRENT



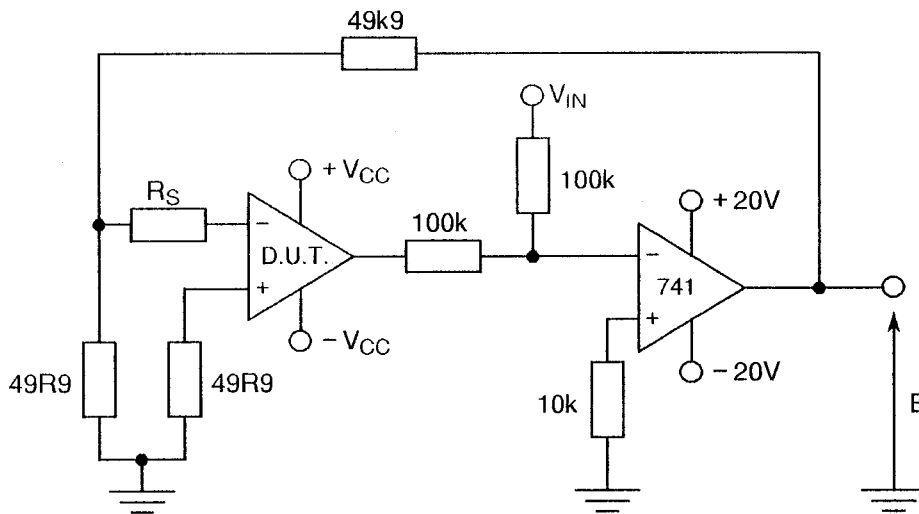
$$I_{+IB1} \text{ (nA)} = \frac{(E_1 \text{ (V)} - E_5 \text{ (V)}) 10^6}{R_S \text{ (k}\Omega)}$$

$$I_{+IB2} \text{ (nA)} = \frac{(E_2 \text{ (V)} - E_6 \text{ (V)}) 10^6}{R_S \text{ (k}\Omega)}$$

NOTES

1. All resistors to be 0.1% tolerance.

FIGURE 4(d) - INPUT (MINUS) BIAS CURRENT



$$I_{-IB1} \text{ (nA)} = \frac{(E_7 \text{ (V)} - E_1 \text{ (V)}) 10^6}{R_S \text{ (k}\Omega)}$$

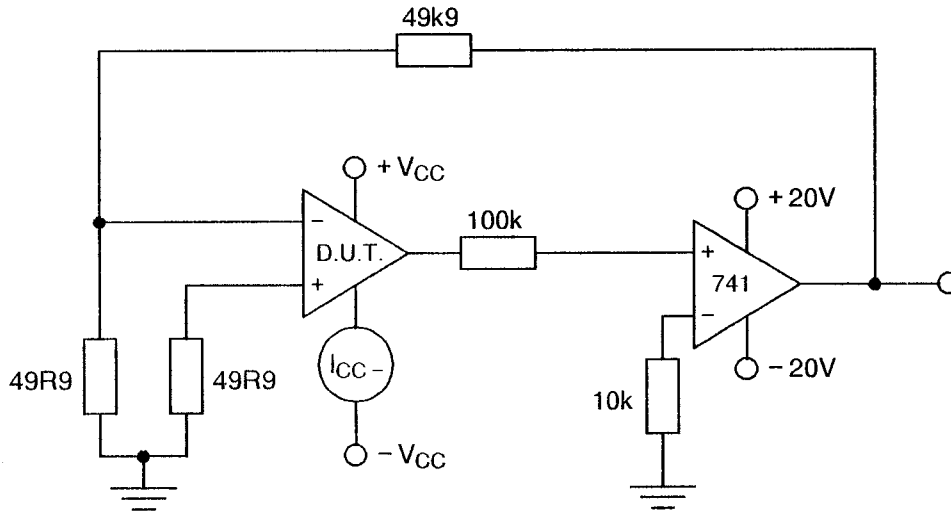
$$I_{-IB2} \text{ (nA)} = \frac{(E_8 \text{ (V)} - E_2 \text{ (V)}) 10^6}{R_S \text{ (k}\Omega)}$$

NOTES

1. All resistors to be 0.1% tolerance.



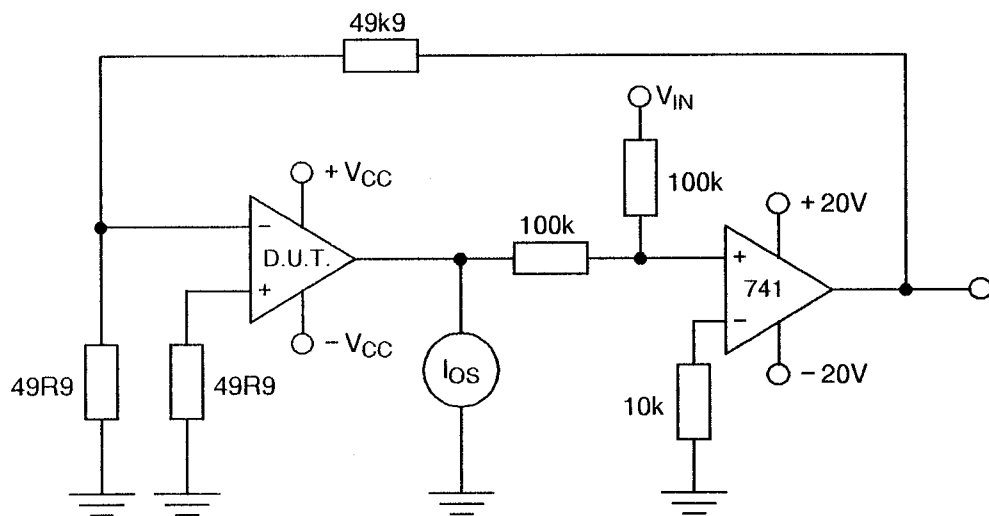
FIGURE 4(e) - SUPPLY CURRENT



NOTES

- 1. All resistors to be 0.1% tolerance.

FIGURE 4(f) - SHORT CIRCUIT OUTPUT CURRENT

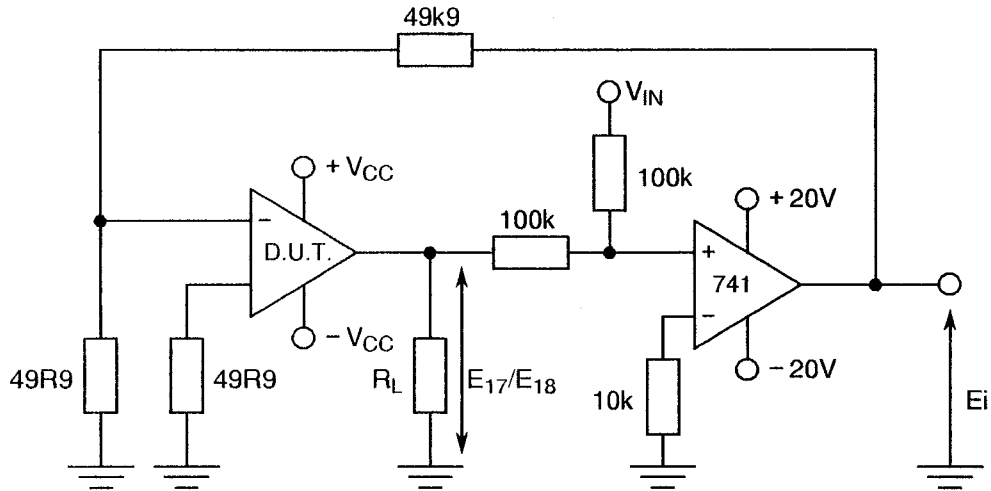


NOTES

- 1. All resistors to be 0.1% tolerance.



FIGURE 4(g) - OUTPUT VOLTAGE SWING
- OPEN LOOP VOLTAGE GAIN

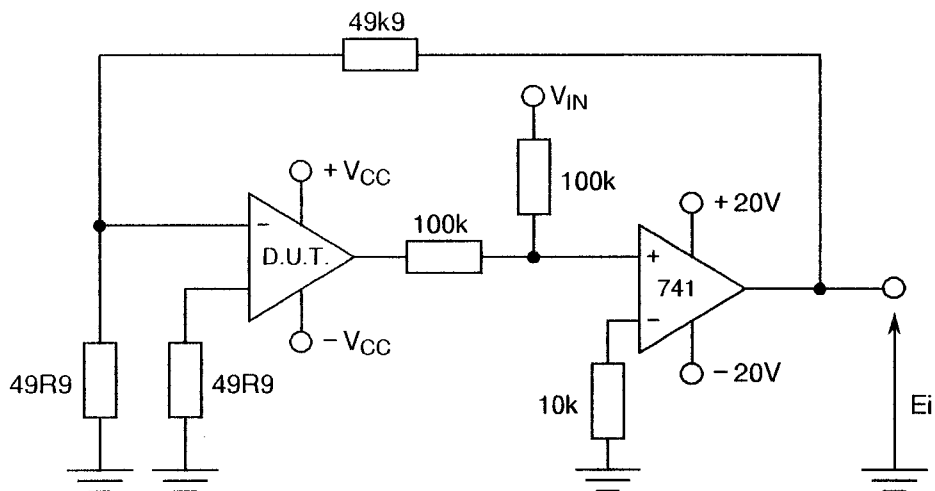


1. $V_{OUT} = (E_{17}, E_{18})$
2. $+A_{VS} = \frac{15}{E_1 - E_9}$, $+A_{VS} = \frac{2}{E_2 - E_{11}}$
3. $-A_{VS} = \frac{15}{E_{10} - E_1}$, $-A_{VS} = \frac{2}{E_{12} - E_2}$

NOTES

1. $E_9, E_{10}, E_{11}, E_{12}$ is in Volts.
2. All resistors to be 0.1% tolerance.

FIGURE 4(h) - POWER SUPPLY REJECTION RATIO



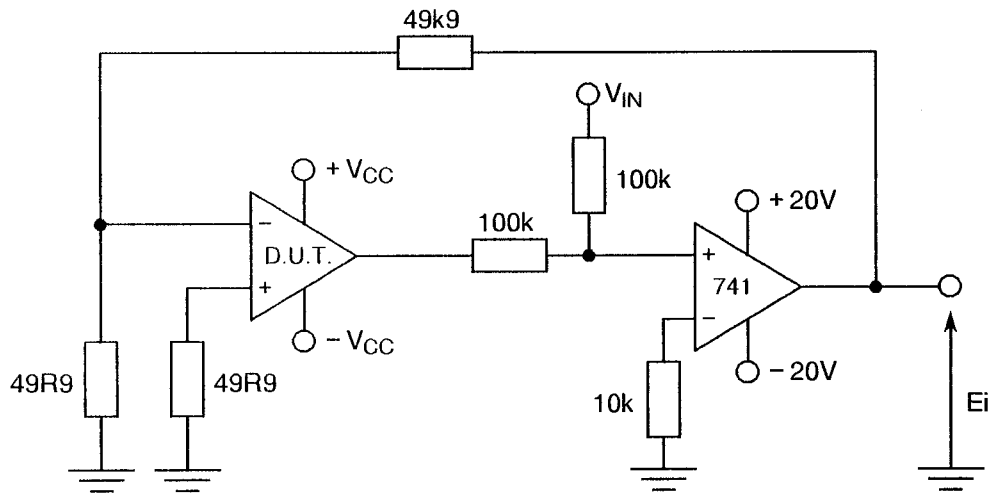
$$+PSRR (\mu V/V) = (E_1 (V) - E_{13} (V)) 10^2, -PSRR (\mu V/V) = (E_1 (V) - E_{14} (V)) 10^2$$

NOTES

1. E_i is measured to four digits accuracy.



FIGURE 4(i) - COMMON MODE REJECTION RATIO



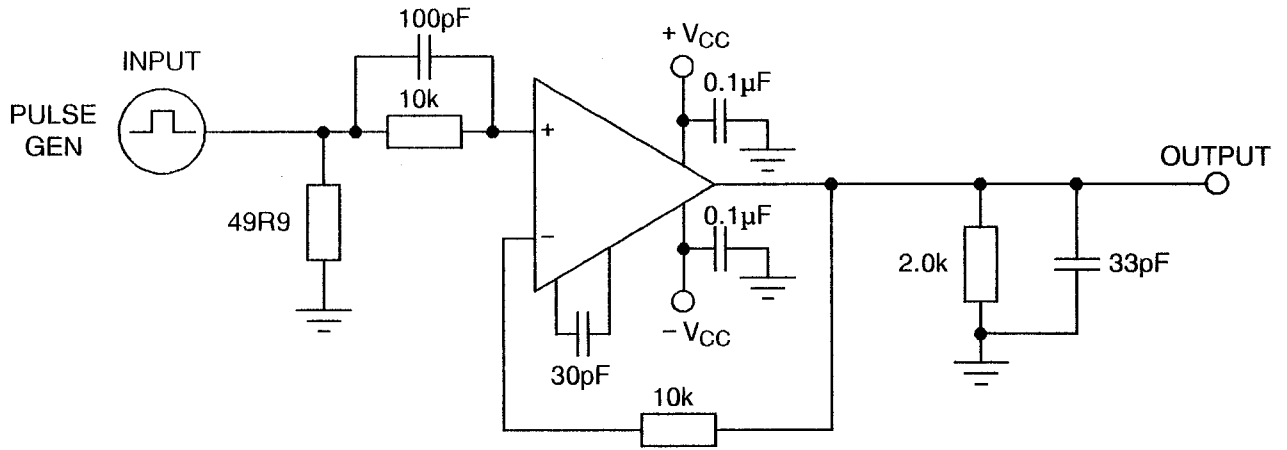
$$\text{CMRR (dB)} = 20 \text{ LOG } \frac{30.10^3}{E_{15} \text{ (V)} - E_{16} \text{ (V)}}$$

NOTES

1. Resistors of 49R9Ω at inputs shall be of 0.01% tolerance matched to 0.001%. Remaining resistors shall be of 0.1% tolerance.



FIGURE 4(k) - DYNAMIC TEST MEASUREMENT CIRCUIT



NOTES

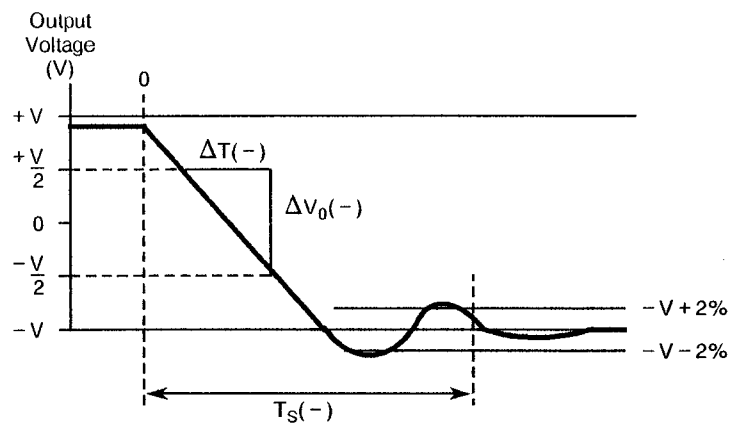
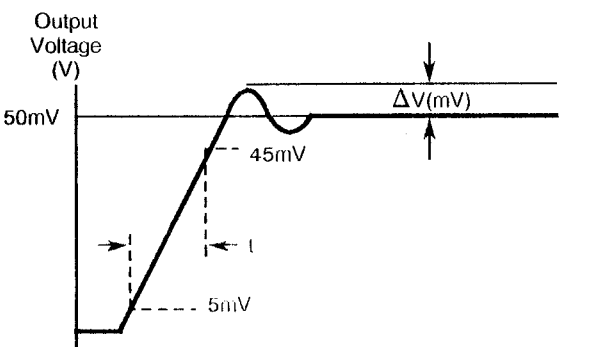
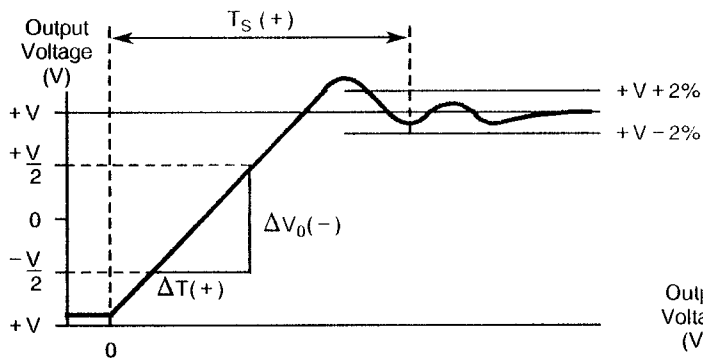
1. Pulse Generator:

- Rise time $\leq 10\text{ns}$
- Repetition rate 1.0kHz (max.)
- Pulse voltage: -5.0V to $+5.0\text{V}$ for slew rate measurement
- Pulse voltage: 50mV for rise time and overshoot measurement

$$SR = \left| \frac{\Delta V_0}{\Delta T} \right| \text{ (V/}\mu\text{s)}$$

$$RT = t \text{ (}\mu\text{s)}$$

$$OS = \frac{\Delta V}{50} \text{ 100(\%)}$$



**TABLE 4 - PARAMETER DRIFT VALUES**

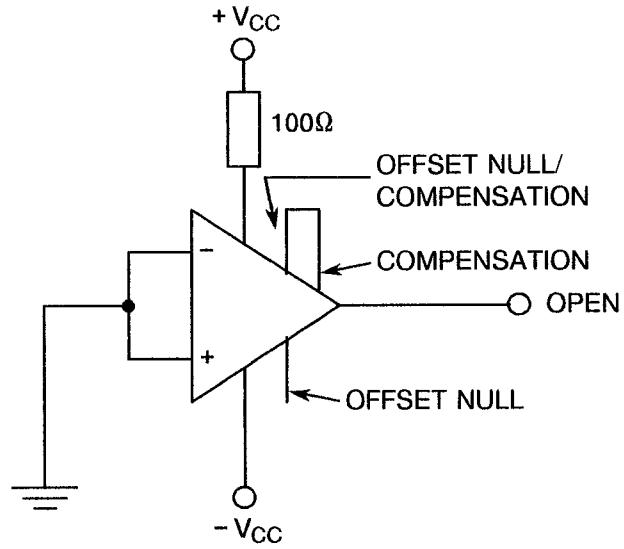
No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS (Δ)	UNIT
1	Input Offset Voltage Change	V_{IO}	As per Table 2	As per Table 2	± 0.5	mV
3	Input Offset Current Change	I_{IO}	As per Table 2	As per Table 2	± 4.0	nA
5	Input Bias Current Change	I_{IB}	As per Table 2	As per Table 2	± 15	nA


TABLE 5 - CONDITIONS FOR BURN-IN

No.	CHARACTERISTICS	SYMBOL	CONDITION	UNIT
1	Ambient Temperature	T_{amb}	$+ 125 \pm 5$	$^{\circ}\text{C}$
2	Supply Voltage	V_{CC}	± 20	V



FIGURE 5 - BURN-IN CIRCUIT



	<p style="text-align: center;">ESA/SCC Detail Specification No. 9101/001</p>	<p style="text-align: right;">PAGE 35 ISSUE 3</p>
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4.8 ENVIRONMENTAL AND ENDURANCE TESTS

4.8.1 Electrical Measurements on Completion of Environmental Tests

The parameters to be measured on completion of environmental tests are scheduled in Table 6. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.8.2 Electrical Measurements at Intermediate Points during Endurance Tests

The parameters to be measured at intermediate points during endurance tests are as scheduled in Table 6 of this specification.

4.8.3 Electrical Measurements on Completion of Endurance Tests

The parameters to be measured on completion of endurance testing are as scheduled in Table 6 of this specification. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.8.4 Conditions for Operating Life Tests

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 9000. The conditions for operating life testing shall be as specified in Table 5 of this specification.

4.8.5 Electrical Circuits for Operating Life Tests


Circuits for use in performing the operating life tests are shown in Figure 5.

4.8.6 Conditions for High Temperature Storage Test

The requirements for the high temperature storage test are specified in ESA/SCC Generic Specification No. 9000. The conditions for high temperature storage shall be $T_{amb} = +150(+0 - 5)$ °C.

**TABLE 6 - ELECTRICAL MEASUREMENTS ON COMPLETION OF ENVIRONMENTAL TESTS AND AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTING**

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	LIMITS		UNIT
					MIN	MAX	
1	Input Offset Voltage	V_{IO}	As per Table 2	As per Table 2	-	2.0	mV
3	Input Offset Current	I_{IO}	As per Table 2	As per Table 2	-	10	nA
5	Input Bias Current	I_{IB}	As per Table 2	As per Table 2	-	75	nA
9	Power Supply Current	I_{CC}	As per Table 2	As per Table 2	-	3.0	mA
12	Open Loop Voltage Gain	$+A_{VS}$	As per Table 2	As per Table 2	50	-	V/mV

	<p>ESA/SCC Detail Specification No. 9101/001</p>	<p>Rev. 'C'</p>	<p>PAGE 37 ISSUE 3</p>
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APPENDIX 'A'

Page 1 of 1

AGREED DEVIATIONS FOR MOTOROLA (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Table 2 (a.c.)	Tests 22 through to 25: Change V_{CC} condition to $V_{CC} = \pm 18V$.
Tables 2, 3(a) and 3(b)	Tests 3 through to 8: Change R_S condition to $R_S = 10k\Omega$.